N-Channel 100 V (D-S) Power MOSFET

PRODUCT SUMMARY $R_{DS(on)}(m\Omega)(Typ.)$ Q_g (Typ.) V_{DS} (V) ID (A)a 88 at $V_{GS} = 10 \text{ V}$ 100 14 4.3 nC 110 at $V_{GS} = 4.5 \text{ V}$

FEATURES

- DT-SJ Power MOSFET
- $\bullet\,$ 100 % $\rm R_{\rm g}$ and UIS Tested
- 100% Avalanche Test
- · Fast Switching

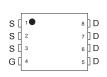
APPLICATIONS

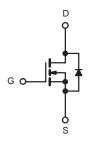
- · AC-DC/DC-DC Converter
- · Isolated DC/DC Converters

PDFN3.3X3.3-8L Pin Configuration

Top View







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 25 °C	1	14	А	
	T _C = 100 °C	I _D	11		
Pulsed Drain Current ^b		I _{DM}	56		
Single Avalanche Energy		E _{AS}	13	mJ	
Maximum Power Dissipation ^c	T _C = 25 °C	P _D	30	W	
	T _C = 100 °C		11.9	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount)d	t ≤ 10 s	R _{thJA}	35	°C/W	
Junction-to-Case (Drain)	Steady State	R _{thJC}	4.2	C/VV	

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{0JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER SYMBOL		TEST CONDITIONS MIN.		TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	100	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	-	3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zara Oata Walkana B. 1 O. 1	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	1 100 μA	
Zero Gate Voltage Drain Current		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	14	-	-	Α	
Drain Source On State Desistance 3	Б	V _{GS} = 10 V, I _D = 7 A	-	88	105	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$	-	110	137	- mΩ	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 5 \text{ V}, I_{D} = 5 \text{ A}$	-	8	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	185	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	-	74	-		
Reverse Transfer Capacitance	C _{rss}		-	6	-		
Total Gate Charge ^c	Qg		-	4.3	-		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	0.41	-	nC	
Gate-Drain Charge ^c	Q _{gd}		-	1.2	-		
Gate Resistance	R_g	f = 1 MHz	-	11.1	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	7	-		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, I_D = 7 \text{ A}, R_g = 3 \Omega$	-	5.2	-	ns	
Turn-Off Delay Time ^c	t _{d(off)}	V _{GS} = 10 V	-	26	-		
Fall Time ^c	t _f		-	8	-		
Drain-Source Body Diode Ratings and	Characteristi	ics ^b (T _C = 25 °C)					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	14	Α	
Pulsed Current	I _{SM}		-	-	56	Α	
Forward Voltage ^a	V _{SD}	I _F = 7 A, V _{GS} = 0 V	-	0.9	-	٧	
Reverse Recovery Time	t _{rr}	L = 7 A di/dt = 500 A/::a	-	11	-	ns	
Reverse Recovery Charge	Q _{rr}	$I_F = 7 \text{ A}, \text{ di/dt } = 500 \text{ A/}\mu\text{s}$	-	17	-	nC	

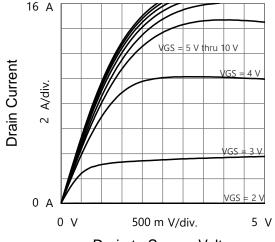
Notes

- a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

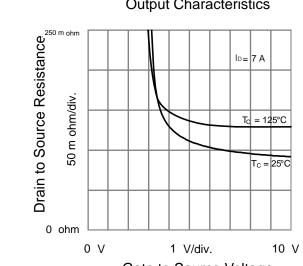
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.



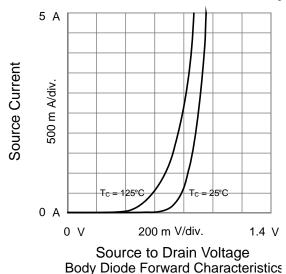
TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

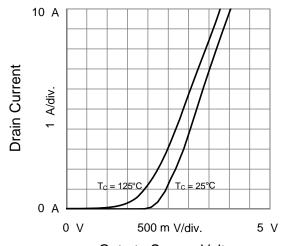


Drain to Source Voltage Output Characteristics

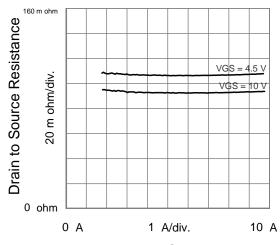


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltag

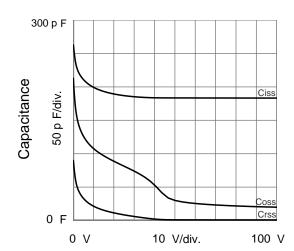




Gate to Source Voltage Transfer Characteristics



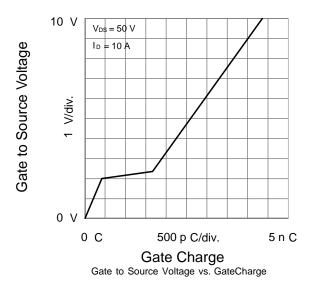
Drain Current

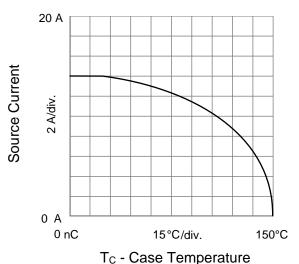


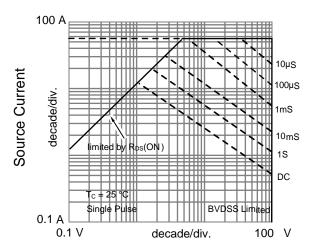
Drain to Source Voltage Capacitances



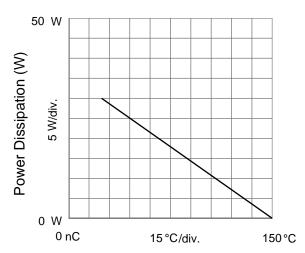
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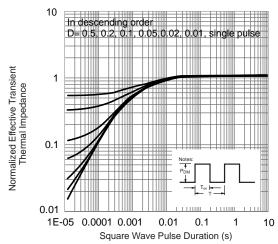




Source to Drain Voltage Safe Operating Area, Junction-to-Case



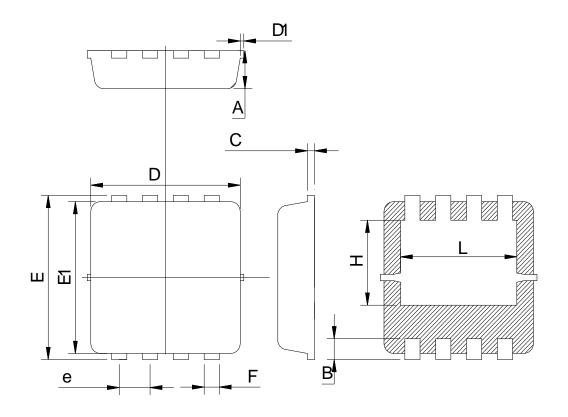
T_C - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



PDFN 3.3X3.3 PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OFMEASURE=MILLIMETER)

Symbol	Min	Тур	Max
А	0.600	0.775	1.000
В	0.20	0.38	0.55
С	0.05	0.15	0.40
D	3.10	3.25	3.50
D1	-	-	0.15
E	3.15	3.35	3.50
E1	2.60	3.10	3.45
е	0.50	0.65	0.80
F	0.15	0.32	0.45
Н	1.25	1.73	2.10
L	2.20	2.45	2.85





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